Kaoru Toko

List of Publications by Citations

245 papers	4,042 citations	32 h-index	49 g-index
273 ext. papers	4,725 ext. citations	2.5 avg, IF	5.7 L-index

#	Paper	IF	Citations
245	Electrical properties of poly-Ge on glass substrate grown by two-step solid-phase crystallization. *Solid-State Electronics*, **2009**, 53, 1159-1164	1.7	116
244	Flux creep and irreversibility line in high-temperature oxide superconductors. *Applied Physics Letters*, **1990**, 56, 2039-2041	3.4	113
243	Investigation of grain boundaries in BaSi2 epitaxial films on Si(1 1 1) substrates using transmission electron microscopy and electron-beam-induced current technique. *Journal of Crystal Growth*, **2012**, 348, 75-79	1.6	108
242	Low-temperature (180 °C) formation of large-grained Ge (111) thin film on insulator using accelerated metal-induced crystallization. *Applied Physics Letters*, **2014**, 104, 022106	3.4	88
241	Effect of amorphous Si capping layer on the hole transport properties of BaSi2 and improved conversion efficiency approaching 10% in p-BaSi2/n-Si solar cells. *Applied Physics Letters*, **2016**, 109, 072103	3.4	82
240	Giant Ge-on-Insulator Formation by Si–Ge Mixing-Triggered Liquid-Phase Epitaxy. *Applied Physics Express*, **2009**, 2, 045503	2.4	79
239	Highly (111)-oriented Ge thin films on insulators formed by Al-induced crystallization. *Applied Physics Letters*, **2012**, 101, 072106	3.4	78
238	Investigation of the recombination mechanism of excess carriers in undoped BaSi2 films on silicon. *Journal of Applied Physics*, **2012**, 112, 083108	2.5	75
237	Multichannel taste sensor using electric potential changes in lipid membranes. *Biosensors and Bioelectronics*, **1994**, 9, 359-64	11.8	69
236	High-quality single-crystal Ge stripes on quartz substrate by rapid-melting-growth. *Applied Physics Letters*, **2009**, 95, 022115	3.4	67
235	Influence of grain size and surface condition on minority-carrier lifetime in undoped n-BaSi2 on Si(111). *Journal of Applied Physics*, **2014**, 115, 193510	2.5	64
234	Temperature dependent metal-induced lateral crystallization of amorphous SiGe on insulating substrate. *Applied Physics Letters*, **2006**, 89, 182120	3.4	64
233	p-BaSi2/n-Si heterojunction solar cells with conversion efficiency reaching 9.0%. *Applied Physics Letters*, **2016**, 108, 152101	3.4	62
232	In-situ heavily p-type doping of over 1020 cm3 in semiconducting BaSi2 thin films for solar cells applications. *Applied Physics Letters*, **2013**, 102, 112107	3.4	59
231	Determination of Bulk Minority-Carrier Lifetime in BaSi2Earth-Abundant Absorber Films by Utilizing a Drastic Enhancement of Carrier Lifetime by Post-Growth Annealing. *Applied Physics Express*, **2013**, 6, 112302	2.4	58
230	Perpendicular magnetic anisotropy of Mn4N films on MgO(001) and SrTiO3(001) substrates. *Journal of Applied Physics*, **2014**, 115, 17A935	2.5	57
229	Ni-imprint induced solid-phase crystallization in Si1−xGex (x: 0–1) on insulator. *Applied Physics Letters*, **2007**, 91, 042111	3.4	56

228	70 ℃ synthesis of high-Sn content (25%) GeSn on insulator by Sn-induced crystallization of amorphous Ge. *Applied Physics Letters*, **2015**, 106, 082109	3.4	55
227	Molecular beam epitaxy of BaSi2 thin films on Si(001) substrates. *Journal of Crystal Growth*, **2012**, 345, 16-21	1.6	53
226	High-hole mobility polycrystalline Ge on an insulator formed by controlling precursor atomic density for solid-phase crystallization. *Scientific Reports*, **2017**, 7, 16981	4.9	51
225	High-Electrical-Conductivity Multilayer Graphene Formed by Layer Exchange with Controlled Thickness and Interlayer. *Scientific Reports*, **2019**, 9, 4068	4.9	48
224	Orientation Control of Large-Grained Si Films on Insulators by Thickness-Modulated Al-Induced Crystallization. *Crystal Growth and Design*, **2013**, 13, 1767-1770	3.5	43
223	Improved photoresponsivity of semiconducting BaSi2 epitaxial films grown on a tunnel junction for thin-film solar cells. *Applied Physics Letters*, **2012**, 100, 152114	3.4	42
222	Chip-size formation of high-mobility Ge strips on SiN films by cooling rate controlled rapid-melting growth. *Applied Physics Letters*, **2011**, 99, 032103	3.4	42
221	Current-voltage characteristics and self-sustained oscillations in dioleyl phosphate-millipore membranes. *Biophysical Chemistry*, **1984**, 20, 39-59	3.5	42
220	Impact of Ba to Si deposition rate ratios during molecular beam epitaxy on carrier concentration and spectral response of BaSi2 epitaxial films. *Journal of Applied Physics*, **2018**, 123, 045703	2.5	41
219	Analysis of the electrical properties of Cr/n-BaSi2 Schottky junction and n-BaSi2/p-Si heterojunction diodes for solar cell applications. *Journal of Applied Physics*, **2014**, 115, 223701	2.5	41
218	Fabrication and characterization of polycrystalline BaSi2 by RF sputtering. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1759-1761		39
217	Electrical characterization and conduction mechanism of impurity-doped BaSi2 films grown on Si(111) by molecular beam epitaxy. *Thin Solid Films*, **2012**, 522, 95-99	2.2	37
216	Selective formation of large-grained, (100)- or (111)-oriented Si on glass by Al-induced layer exchange. *Journal of Applied Physics*, **2014**, 115, 094301	2.5	36
215	Sign of the spin-polarization in cobalt-iron nitride films determined by the anisotropic magnetoresistance effect. *Journal of Applied Physics*, **2014**, 116, 053912	2.5	35
214	Influence of air exposure duration and a-Si capping layer thickness on the performance of p-BaSi2/n-Si heterojunction solar cells. *AIP Advances*, **2016**, 6, 085107	1.5	34
213	Operation of BaSi2 homojunction solar cells on p+-Si(111) substrates and the effect of structure parameters on their performance. *Applied Physics Express*, **2019**, 12, 041005	2.4	32
212	Epitaxial growth and magnetic characterization of ferromagnetic Co4N thin films on SrTiO3(001) substrates by molecular beam epitaxy. *Journal of Crystal Growth*, **2011**, 336, 40-43	1.6	32
211	Relation of growth process to spatial patterns of electric potential and enzyme activity in bean roots. *Biophysical Chemistry*, **1987**, 27, 39-58	3.5	32

210	Oscillations of electrical potential along a root of a higher plant. *Biophysical Journal*, **1990**, 57, 269-79	2.9	30
209	Fabrication and characterization of BaSi2epitaxial films over 1 μm in thickness on Si(111). *Japanese Journal of Applied Physics*, **2014**, 53, 04ER04	1.4	29
208	On the oscillatory phenomenon in an oil/water interface. *Biophysical Chemistry*, **1985**, 22, 151-8	3.5	29
207	Improving carrier mobility of polycrystalline Ge by Sn doping. *Scientific Reports*, **2018**, 8, 14832	4.9	28
206	Precipitation control and activation enhancement in boron-doped p+-BaSi2 films grown by molecular beam epitaxy. *Applied Physics Letters*, **2014**, 104, 252104	3.4	27
205	Low-Temperature (~ 250℃) Cu-Induced Lateral Crystallization of Amorphous Ge on Insulator. *Electrochemical and Solid-State Letters*, **2011**, 14, H274		27
204	Formation of polycrystalline BaSi2 films by radio-frequency magnetron sputtering for thin-film solar cell applications. *Thin Solid Films*, **2013**, 534, 116-119	2.2	26
203	Improved Surface Quality of the Metal-Induced Crystallized Ge Seed Layer and Its Influence on Subsequent Epitaxy. *Crystal Growth and Design*, **2015**, 15, 1535-1539	3.5	26
202	Evaluation of potential variations around grain boundaries in BaSi2 epitaxial films by Kelvin probe force microscopy. *Applied Physics Letters*, **2013**, 103, 142113	3.4	26
201	Al-Induced oriented-crystallization of Si films on quartz and its application to epitaxial template for Ge growth. *Solid-State Electronics*, **2011**, 60, 7-12	1.7	26
200	Perpendicular magnetic anisotropy in CoxMn4−xN (x = 0 and 0.2) epitaxial films and possibility of tetragonal Mn4N phase. *AIP Advances*, **2016**, 6, 056201	1.5	25
199	p-BaSi2/n-Si heterojunction solar cells on Si(001) with conversion efficiency approaching 10%: comparison with Si(111). *Applied Physics Express*, **2018**, 11, 062301	2.4	25
198	Negative spin polarization at the Fermi level in Fe4N epitaxial films by spin-resolved photoelectron spectroscopy. *Journal of Applied Physics*, **2012**, 112, 013911	2.5	25
197	Stabilization effect of protons and divalent cations on membrane structures of lipids. *Biophysical Chemistry*, **1981**, 14, 11-23	3.5	25
196	Direct synthesis of multilayer graphene on an insulator by Ni-induced layer exchange growth of amorphous carbon. *Applied Physics Letters*, **2017**, 110, 033108	3.4	24
195	Simple way of finding Ba to Si deposition rate ratios for high photoresponsivity in BaSi2 films by Raman spectroscopy. *Applied Physics Express*, **2019**, 12, 055506	2.4	24
194	N-type doping of BaSi2 epitaxial films by phosphorus ion implantation and thermal annealing. *Thin Solid Films*, **2014**, 557, 90-93	2.2	23
193	Evaluation of band offset at amorphous-Si/BaSi2 interfaces by hard x-ray photoelectron spectroscopy. *Journal of Applied Physics*, **2016**, 119, 165304	2.5	23

192	Metal-induced layer exchange of group IV materials. *Journal Physics D: Applied Physics*, **2020**, 53, 373002	3	22
191	X-ray magnetic circular dichroism of ferromagnetic Co4N epitaxial films on SrTiO3(001) substrates grown by molecular beam epitaxy. *Applied Physics Letters*, **2011**, 99, 252501	3.4	22
190	Defect-free single-crystal Ge island arrays on insulator by rapid-melting-growth combined with seed-positioning technique. *Applied Physics Letters*, **2009**, 95, 112107	3.4	21
189	Potential variations around grain boundaries in impurity-doped BaSi2 epitaxial films evaluated by Kelvin probe force microscopy. *Journal of Applied Physics*, **2014**, 116, 123709	2.5	20
188	N-type doping of BaSi2 epitaxial films by arsenic ion implantation through a dose-dependent carrier generation mechanism. *Thin Solid Films*, **2014**, 567, 105-108	2.2	20
187	High-quality multilayer graphene on an insulator formed by diffusion controlled Ni-induced layer exchange. *Applied Physics Letters*, **2017**, 111, 243104	3.4	20
186	High hole mobility (500 cm2 V−1 s−1) polycrystalline Ge films on GeO2-coated glass and plastic substrates. *Applied Physics Express*, **2019**, 12, 015508	2.4	20
185	Control of grain size and crystallinity of poly-Si films on quartz by Al-induced crystallization. *CrystEngComm*, **2017**, 19, 2305-2311	3.3	19
184	Magnetic and magneto-transport properties of Mn4N thin films by Ni substitution and their possibility of magnetic compensation. *Journal of Applied Physics*, **2019**, 125, 213902	2.5	19
183	Vertically Aligned Ge Nanowires on Flexible Plastic Films Synthesized by (111)-Oriented Ge Seeded Vapor-Liquid-Solid Growth. *ACS Applied Materials & Interfaces*, **2015**, 7, 18120-4	9.5	19
182	Lattice and grain-boundary diffusions of boron atoms in BaSi2 epitaxial films on Si(111). *Journal of Applied Physics*, **2013**, 113, 053511	2.5	19
181	Dependence of crystal orientation in Al-induced crystallized poly-Si layers on SiO2 insertion layer thickness. *Journal of Crystal Growth*, **2012**, 356, 65-69	1.6	19
180	Indentation-induced low-temperature solid-phase crystallization of Si1−xGex (x=0−1) on insulator. *Applied Physics Letters*, **2009**, 94, 192106	3.4	19
179	Advanced solid-phase crystallization for high-hole mobility (450 cm2V−1s−1) Ge thin film on insulator. *Applied Physics Express*, **2018**, 11, 031302	2.4	18
178	X-ray magnetic circular dichroism for CoxFe4−xN (x = 0, 3, 4) films grown by molecular beam epitaxy. *Journal of Applied Physics*, **2014**, 115, 17C712	2.5	18
177	Single-crystalline (100) Ge networks on insulators by rapid-melting growth along hexagonal mesh-pattern. *Applied Physics Letters*, **2011**, 98, 042101	3.4	18
176	Polycrystalline thin-film transistors fabricated on high-mobility solid-phase-crystallized Ge on glass. *Applied Physics Letters*, **2019**, 114, 212107	3.4	17
175	Direct synthesis of highly textured Ge on flexible polyimide films by metal-induced crystallization. *Applied Physics Letters*, **2014**, 104, 262107	3.4	17

174	Orientation control of Ge thin films by underlayer-selected Al-induced crystallization. *CrystEngComm*, **2014**, 16, 2578	3.3	17
173	Low temperature synthesis of highly oriented p-type Si1-xGex (x: 0□1) on an insulator by Al-induced layer exchange. *Journal of Applied Physics*, **2017**, 122, 155305	2.5	17
172	(100) Orientation-Controlled Ge Giant-Stripes on Insulating Substrates by Rapid-Melting Growth Combined with Si Micro-Seed Technique. *Applied Physics Express*, **2010**, 3, 075603	2.4	17
171	Measurement of valence-band offset at native oxide/BaSi2 interfaces by hard x-ray photoelectron spectroscopy. *Journal of Applied Physics*, **2016**, 119, 025306	2.5	17
170	Thermoelectric Inorganic SiGe Film Synthesized on Flexible Plastic Substrate. *ACS Applied Energy Materials*, **2018**,	6.1	17
169	Local electronic states of Fe4N films revealed by x-ray absorption spectroscopy and x-ray magnetic circular dichroism. *Journal of Applied Physics*, **2015**, 117, 193906	2.5	16
168	Epitaxial growth and magnetic properties of Fe 4□x Mn x N thin films grown on MgO(0 0 1) substrates by molecular beam epitaxy. *Journal of Crystal Growth*, **2018**, 489, 20-23	1.6	16
167	Detection of local vibrational modes induced by intrinsic defects in undoped BaSi2 light absorber layers using Raman spectroscopy. *Journal of Applied Physics*, **2018**, 124, 025301	2.5	16
166	Evaluation of minority carrier diffusion length of undoped n-BaSi2epitaxial thin films on Si(001) substrates by electron-beam-induced-current technique. *Japanese Journal of Applied Physics*, **2014**, 53, 078004	1.4	16
165	Double-Layered Ge Thin Films on Insulators Formed by an Al-Induced Layer-Exchange Process. *Crystal Growth and Design*, **2013**, 13, 3908-3912	3.5	16
164	Large-Grained Polycrystalline (111) Ge Films on Insulators by Thickness-Controlled Al-Induced Crystallization. *ECS Journal of Solid State Science and Technology*, **2013**, 2, Q195-Q199	2	16
163	High Quality Single-Crystalline Ge-Rich SiGe on Insulator Structures by Si-Doping Controlled Rapid Melting Growth. *Applied Physics Express*, **2010**, 3, 031301	2.4	16
162	Defect-free Ge-on-insulator with (100), (110), and (111) orientations by growth-direction-selected rapid-melting growth. *Applied Physics Letters*, **2010**, 97, 152101	3.4	16
161	Growth and electric current loops in plants. *Biophysical Chemistry*, **1989**, 33, 161-76	3.5	16
160	Millimeter-sized magnetic domains in perpendicularly magnetized ferrimagnetic Mn4N thin films grown on SrTiO3. *Japanese Journal of Applied Physics*, **2018**, 57, 120310	1.4	16
159	Metal Catalysts for Layer-Exchange Growth of Multilayer Graphene. *ACS Applied Materials & Interfaces*, **2018**, 10, 41664-41669	9.5	16
158	Formation of BaSi2 heterojunction solar cells using transparent MoOx hole transport layers. *Applied Physics Letters*, **2015**, 106, 122104	3.4	15
157	Strong correlation between uniaxial magnetic anisotropic constant and in-plane tensile strain in Mn4N epitaxial films. *AIP Advances*, **2020**, 10, 025117	1.5	15

156	Structural study on phosphorus doping of BaSi2 epitaxial films by ion implantation. *Thin Solid Films*, **2013**, 534, 470-473	2.2	15
155	Mechanism of strain relaxation in BaSi2 epitaxial films on Si(111) substrates during post-growth annealing and application for film exfoliation. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1677-1680		15
154	Negative Anisotropic Magnetoresistance in $gamma'$-Fe$_{4}$N Epitaxial Films on SrTiO$_{3}$(001) Grown by Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **2012**, 51, 068001	1.4	15
153	Marked enhancement of the photoresponsivity and minority-carrier lifetime of BaSi2 passivated with atomic hydrogen. *Physical Review Materials*, **2019**, 3,	3.2	15
152	Molecular beam epitaxy growth of Mn4−xNixN thin films on MgO(0 0 1) substrates and their magnetic properties. *Journal of Crystal Growth*, **2019**, 507, 163-167	1.6	15
151	Significant photoresponsivity enhancement of polycrystalline BaSi2 films formed on heated Si(111) substrates by sputtering. *Applied Physics Express*, **2018**, 11, 071401	2.4	15
150	Effect of p-BaSi2layer thickness on the solar cell performance of p-BaSi2/n-Si heterojunction solar cells. *Japanese Journal of Applied Physics*, **2017**, 56, 05DB03	1.4	14
149	Sb-doped crystallization of densified precursor for n-type polycrystalline Ge on an insulator with high carrier mobility. *Applied Physics Letters*, **2019**, 114, 082105	3.4	14
148	Magnetic reversal in rare-earth free Mn4−xNixN epitaxial films below and above Ni composition needed for magnetic compensation around room temperature. *Journal of Applied Physics*, **2020**, 127, 043903	2.5	14
147	Orientation control of intermediate-composition SiGe on insulator by low-temperature Al-induced crystallization. *Scripta Materialia*, **2016**, 122, 86-88	5.6	14
146	Photoresponse properties of undoped BaSi2epitaxial layers on n+-BaSi2/p+-Si(001) by molecular beam epitaxy. *Japanese Journal of Applied Physics*, **2014**, 53, 058007	1.4	14
145	Fabrication and characterizations of phosphorus-doped n-type BaSi2 epitaxial films grown by molecular beam epitaxy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1753-1755		14
144	Spectroscopic evidence of photogenerated carrier separation by built-in electric field in Sb-doped n-BaSi2/B-doped p-BaSi2homojunction diodes. *Japanese Journal of Applied Physics*, **2018**, 57, 050310	1.4	14
143	Temperature dependent Al-induced crystallization of amorphous Ge thin films on SiO2 substrates. *Journal of Crystal Growth*, **2013**, 372, 189-192	1.6	13
142	Molecular beam epitaxy of boron doped p-type BaSi2 epitaxial films on Si(111) substrates for thin-film solar cells. *Journal of Crystal Growth*, **2013**, 378, 201-204	1.6	13
141	Rotational and vibrational temperatures in a hydrogen discharge with a magnetic X-point. *Physics of Plasmas*, **2012**, 19, 123503	2.1	13
140	High-quality formation of multiply stacked SiGe-on-insulator structures by temperature-modulated successive rapid-melting-growth. *Applied Physics Letters*, **2013**, 102, 092102	3.4	13
139	Hard x-ray photoelectron spectroscopy study on valence band structure of semiconducting BaSi2. *Journal of Applied Physics*, **2013**, 114, 123702	2.5	13

138	Three-step growth of highly photoresponsive BaSi2 light absorbing layers with uniform Ba to Si atomic ratios. *Journal of Applied Physics*, **2019**, 126, 215301	2.5	13
137	Low-Temperature (400 °C) Synthesis of Multilayer Graphene by Metal-Assisted Sputtering Deposition. *ACS Omega*, **2019**, 4, 6677-6680	3.9	12
136	Growth promotion of Al-induced crystallized Ge films on insulators by insertion of a Ge membrane below the Al layer. *Thin Solid Films*, **2014**, 557, 143-146	2.2	12
135	Low-temperature crystallization of amorphous silicon and amorphous germanium by soft X-ray irradiation. *Thin Solid Films*, **2013**, 534, 334-340	2.2	12
134	Silver-induced layer exchange for polycrystalline germanium on a flexible plastic substrate. *Journal of Applied Physics*, **2017**, 122, 215305	2.5	12
133	Mesh-shape-and-size controlled rapid-melting growth for the formation of single-crystalline (100), (110), and (111) Ge networks on insulators. *Applied Physics Letters*, **2011**, 98, 182107	3.4	12
132	Epitaxial growth and magnetic properties of NixFe4-xN (x = 0, 1, 3, and 4) films on SrTiO3(001) substrates. *Journal of Applied Physics*, **2016**, 120, 083907	2.5	12
131	High-electron-mobility (370 cm/Vs) polycrystalline Ge on an insulator formed by As-doped solid-phase crystallization. *Scientific Reports*, **2019**, 9, 16558	4.9	12
130	Manipulation of saturation magnetization and perpendicular magnetic anisotropy in epitaxial CoxMn4−xN films with ferrimagnetic compensation. *Physical Review B*, **2020**, 101,	3.3	11
129	Molecular beam epitaxy of Co Fe4−N (0.4. *Journal of Crystal Growth*, **2012**, 357, 53-57	1.6	11
128	Magnetic compensation at two different composition ratios in rare-earth-free Mn4−xCoxN ferrimagnetic films. *Physical Review Materials*, **2020**, 4,	3.2	11
127	Enhanced spectral response of semiconducting BaSi2 films by oxygen incorporation. *Thin Solid Films*, **2017**, 629, 17-21	2.2	10
126	Solid-phase crystallization of densified amorphous GeSn leading to high hole mobility (540 cm2/V s). *Applied Physics Letters*, **2019**, 114, 112110	3.4	10
125	Influence of Substrate on Crystal Orientation of Large-Grained Si Thin Films Formed by Metal-Induced Crystallization. *International Journal of Photoenergy*, **2015**, 2015, 1-7	2.1	10
124	Electronic structures and magnetic moments of Co3FeN thin films grown by molecular beam epitaxy. *Applied Physics Letters*, **2013**, 103, 232403	3.4	10
123	Spontaneous formation of the spatial pattern of electric potential in biological systems. *Ferroelectrics*, **1988**, 86, 269-279	0.6	10
122	Impact of deposition pressure and two-step growth technique on the photoresponsivity enhancement of polycrystalline BaSi2 films formed by sputtering. *Applied Physics Express*, **2019**, 12, 021004	2.4	9
121	80 °C synthesis of thermoelectric nanocrystalline Ge film on flexible plastic substrate by Zn-induced layer exchange. *Applied Physics Express*, **2019**, 12, 055501	2.4	9

120	Perpendicular magnetic anisotropy in ferrimagnetic Mn4N films grown on (LaAlO3)0.3(Sr2TaAlO6)0.7(0□0□1) substrates by molecular beam epitaxy. *Journal of Crystal Growth*, **2020**, 535, 125566	1.6	9
119	Characterization of defect levels in undoped n-BaSi2epitaxial films on Si(111) by deep-level transient spectroscopy. *Japanese Journal of Applied Physics*, **2015**, 54, 07JE01	1.4	9
118	High-hole mobility Si1-xGex (0.1 □x □1) on an insulator formed by advanced solid-phase crystallization. *Journal of Alloys and Compounds*, **2018**, 766, 417-420	5.7	9
117	Effects of flexible substrate thickness on Al-induced crystallization of amorphous Ge thin films. *Thin Solid Films*, **2015**, 583, 221-225	2.2	8
116	Zn-induced layer exchange of p- and n-type nanocrystalline SiGe layers for flexible thermoelectrics. *Applied Physics Letters*, **2020**, 116, 182105	3.4	8
115	Atomic hydrogen passivation for photoresponsivity enhancement of boron-doped p-BaSi2 films and performance improvement of boron-doped p-BaSi2/n-Si heterojunction solar cells. *Journal of Applied Physics*, **2020**, 127, 233104	2.5	8
114	Self-organization of Ge(111)/Al/glass structures through layer exchange in metal-induced crystallization. *CrystEngComm*, **2014**, 16, 9590-9595	3.3	8
113	Multilayer graphene on insulator formed by Co-induced layer exchange. *Japanese Journal of Applied Physics*, **2017**, 56, 05DE03	1.4	8
112	Dynamic property of membrane formation in a protoplasmic droplet of Nitella. *Biophysical Chemistry*, **1985**, 21, 295-313	3.5	8
111	Negative Anisotropic Magnetoresistance in □Fe4N Epitaxial Films on SrTiO3(001) Grown by Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **2012**, 51, 068001	1.4	8
110	Strain effects on polycrystalline germanium thin films. *Scientific Reports*, **2021**, 11, 8333	4.9	8
109	Investigation of electrically active defects in undoped BaSi2 light absorber layers using deep-level transient spectroscopy. *Japanese Journal of Applied Physics*, **2018**, 57, 075801	1.4	8
108	Investigation of native defects in BaSi2 epitaxial films by electron paramagnetic resonance. *Applied Physics Express*, **2019**, 12, 061005	2.4	7
107	High photoresponsivity in a GaAs film synthesized on glass using a pseudo-single-crystal Ge seed layer. *Applied Physics Letters*, **2019**, 114, 142103	3.4	7
106	Growth of BaSi2 continuous films on Ge(111) by molecular beam epitaxy and fabrication of p-BaSi2/n-Ge heterojunction solar cells. *Japanese Journal of Applied Physics*, **2017**, 56, 05DB02	1.4	7
105	Diffusion coefficients of impurity atoms in BaSi2epitaxial films grown by molecular beam epitaxy. *Japanese Journal of Applied Physics*, **2014**, 53, 04ER02	1.4	7
104	Lattice and grain-boundary diffusions of impurity atoms in BaSi2 epitaxial layers grown by molecular beam epitaxy. *Journal of Crystal Growth*, **2013**, 378, 189-192	1.6	7
103	Structural characterization of polycrystalline Ge thin films on insulators formed by diffusion-enhanced Al-induced layer exchange. *Japanese Journal of Applied Physics*, **2014**, 53, 04EH03	1.4	7

102	Molecular Beam Epitaxy of BaSi$_{2}$ Films with Grain Size over 4 mum on Si(111). *Japanese Journal of Applied Physics*, **2012**, 51, 098003	1.4	7
101	Growth and magnetic properties of epitaxial Fe4N films on insulators possessing lattice spacing close to Si(001) plane. *Journal of Crystal Growth*, **2016**, 455, 66-70	1.6	7
100	Improving the photoresponse spectra of BaSi2 layers by capping with hydrogenated amorphous Si layers prepared by radio-frequency hydrogen plasma. *AIP Advances*, **2018**, 8, 055306	1.5	7
99	Boron-doped p-BaSi2/n-Si solar cells formed on textured n-Si(0 0 1) with a pyramid structure consisting of {1 1 1} facets. *Journal of Crystal Growth*, **2017**, 475, 186-191	1.6	6
98	Fabrication of As-doped n-type BaSi2 epitaxial films grown by molecular beam epitaxy. *Japanese Journal of Applied Physics*, **2020**, 59, SFFA01	1.4	6
97	Improved thermoelectric performance of flexible p-type SiGe films by B-doped Al-induced layer exchange. *Journal Physics D: Applied Physics*, **2020**, 53, 075105	3	6
96	Reduction in interface defect density in p-BaSi2/n-Si heterojunction solar cells by a modified pretreatment of the Si substrate. *Japanese Journal of Applied Physics*, **2018**, 57, 025501	1.4	6
95	Control of electrical properties of BaSi2 thin films by alkali-metal doping using alkali-metal fluorides. *Thin Solid Films*, **2016**, 603, 218-223	2.2	6
94	Investigation of defect levels in BaSi2 epitaxial films by photoluminescence and the effect of atomic hydrogen passivation. *Journal of Physics Communications*, **2019**, 3, 075005	1.2	6
93	Large-grained (111)-oriented Si/Al/SiO2 structures formed by diffusion-controlled Al-induced layer exchange. *Thin Solid Films*, **2014**, 557, 147-150	2.2	6
92	Transfer-free synthesis of highly ordered Ge nanowire arrays on glass substrates. *Applied Physics Letters*, **2015**, 107, 133102	3.4	6
91	Potential variation around grain boundaries in BaSi2 films grown on multicrystalline silicon evaluated using Kelvin probe force microscopy. *Journal of Applied Physics*, **2014**, 116, 235301	2.5	6
90	Al-induced crystallization of amorphous Ge thin films on conducting layer coated glass substrates. *Japanese Journal of Applied Physics*, **2014**, 53, 04EH01	1.4	6
89	Structural Study of BF$_{2}$ Ion Implantation and Post Annealing of BaSi$_{2}$ Epitaxial Films. *Japanese Journal of Applied Physics*, **2011**, 50, 121202	1.4	6
88	Nucleation-Controlled Metal-Induced Lateral Crystallization of Amorphous Si1-xGexwith Whole Ge Fraction on Insulator. *Japanese Journal of Applied Physics*, **2008**, 47, 1876-1879	1.4	6
87	Electrical characteristics in an excitable element of lipid membrane. *Biophysical Chemistry*, **1991**, 41, 143-56	3.3	6
86	Impact of radio-frequency power on the photoresponsivity enhancement of BaSi2 films formed by sputtering. *Applied Physics Express*, **2020**, 13, 085511	2.4	6
85	Molecular Beam Epitaxy of BaSi2Films with Grain Size over 4 μm on Si(111). *Japanese Journal of Applied Physics*, **2012**, 51, 098003	1.4	6

84	Influence of Ba-to-Si deposition rate ratios on the electrical and optical properties of B-doped BaSi2 epitaxial films. *Japanese Journal of Applied Physics*, **2020**, 59, SFFA04	1.4	6
83	350 °C synthesis of high-quality multilayer graphene on an insulator using Ni-induced layer exchange. *Applied Physics Express*, **2020**, 13, 055502	2.4	6
82	Formation of high-photoresponsivity BaSi2 films on glass substrate by radio-frequency sputtering for solar cell applications. *Journal Physics D: Applied Physics*, **2021**, 54, 135106	3	6
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